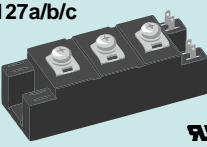
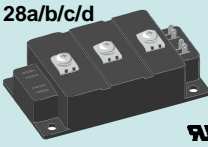
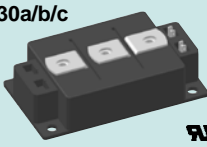
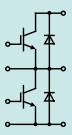
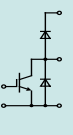
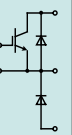
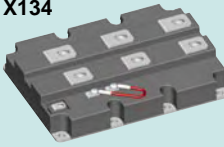

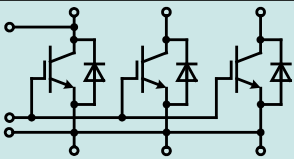


IGBT Modules

NPT IGBT Modules												
								Outline drawings on pages O-30...O-52 See data sheet for pin arrangement				
Type	V _{CES} V	I _{C25} IGBT T _C = 25°C A	I _{C80} IGBT T _C = 80°C A	V _{CE(sat)} typ IGBT T _J = 25°C V	E _{off} IGBT T _J = 125°C mJ	R _{thJC} IGBT K/W	I _{F25} diode T _C = 25°C A	I _{F80} diode T _C = 80°C A	Fig. No.			
1200 V Half Bridge, NPT												
MII 75-12A3	1200	90	60	2.2	5.6	0.33	100	60	X127a			
MII 100-12A3		135	90	2.2	10.5	0.22	150	100				
MII 145-12A3		160	110	2.2	15.0	0.18	150	100	X128a			
MII 150-12A4		180	120	2.2	11.5	0.17	200	130				
MII 200-12A4		270	180	2.2	21.0	0.11	300	200				
MII 300-12A4		330	220	2.2	29.0	0.09	450	270				
1200 V Boost Chopper, NPT												
MID 75-12A3	1200	90	60	2.2	5.6	0.33	100	60	X127b			
MID 100-12A3		135	90	2.2	10.5	0.22	150	100				
MID 145-12A3		160	110	2.2	15.0	0.18	150	100	X128b			
MID 150-12A4		180	120	2.2	11.5	0.17	200	130				
MID 200-12A4		270	180	2.2	21.0	0.11	300	200				
MID 300-12A4		330	220	2.2	29.0	0.09	450	270				
MID 550-12A4		670	460	2.3	59.0	0.05	750	460				
1200 V Buck Chopper, NPT												
MDI 75-12A3	1200	90	60	2.2	5.6	0.33	100	60	X127c			
MDI 100-12A3		135	90	2.2	10.5	0.22	150	100				
MDI 145-12A3		160	110	2.2	15.0	0.18	150	100	X128c			
MDI 150-12A4		180	120	2.2	11.5	0.17	200	130				
MDI 200-12A4		270	180	2.2	21.0	0.11	300	200				
MDI 300-12A4		330	220	2.2	29.0	0.09	450	270				
MDI 550-12A4		670	460	2.3	59.0	0.05	750	460				
1200 V Half Bridge, NPT³												
MII 300-12E4	1200	280	200	2.0	20.0	0.11	300	190	X130a			
MII 400-12E4		420	300	2.2	30.0	0.08	450	290				
1200 V Boost Chopper, NPT³												
MID 400-12E4	1200	420	300	2.2	30.0	0.08	450	290	X130b			
1200 V Buck Chopper, NPT³												
MDI 400-12E4	1200	420	300	2.2	30.0	0.08	450	290	X130c			

High Power Single Switch									
						Package style Outline drawings on pages O-30...O-52			
<ul style="list-style-type: none"> • low loss and smooth switching • AISiC base plate for high power cycling capacity • AIN substrate for low thermal resistance 									
Type	V _{CES} V	I _{C25} IGBT T _C = 25°C A	I _{C80} IGBT T _C = 80°C A	V _{CE(sat)} typ IGBT T _J = 25°C V	E _{off} IGBT T _J = 125°C mJ	R _{thJC} IGBT K/W	I _{F25} diode T _C = 25°C A	I _{F80} diode T _C = 80°C A	Fig. No.
MIO 1800-17E10	1700	2500	1800	2.3	670	0,009	tbd	1800	X134
MIO 2400-17E10	1700	3300	2400	2.3	980	0,007		2400	
MIO 1200-25E10	2500	1650	1200	2.5	1250	0,009		1200	
MIO 1500-25E10	2500	2100	1500	2.7	1450	0,008		1500	
MIO 1200-33E10	3300	1650	1200	3.1	1950	0,0085		1200	
High Voltage Package with enlarged strike and creepage distance									
MIO 1200-33E11	3300	1650	1200	3.1	2000	0,0085	tbd	1200	X135
MIO 600-65E11	6500	840	600	4.2	3500	0,011		600	